Supporting Information

Optimization and Device Application Potential of Oxide-Metal-Oxide Transparent Electrode Structure

Yun Cheol Kim, a Su Jeong Lee, a Hanearl Jung, b Bo-Eun Park, b Hyungjun Kim, b Woong Lee* c
and Jae-Min Myoung*a

a Department of Materials Science and Engineering, Yonsei University, 50 Yonsei-ro, Seodaemun-gu, Seoul 120-749, Korea

b School of Electrical and Electronic Engineering, Yonsei University, 50 Yonsei-ro, Seodaemun-gu, Seoul 120-749, Korea

c School of Materials Science and Engineering, Changwon National University, 20 Changwondaehak-ro, Changwon, Gyeongnam 641-774, Korea

*E-mail address: woonglee@changwon.ac.kr, jmmyoung@yonsei.ac.kr
Fig. S1 SEM micrographs showing the morphological evolution of the Ag mid-layer with increasing thickness.
Fig. S2 Cross-sectional structure of the optimized IZO-Ag-IZO electrode as identified by: (a) XPS depth profile, (b) cross-sectional TEM (JSM-2100F, JEOL) contrast image, and (c) HRTEM image. It is seen that top and bottom IZO layers (amorphous) and Ag mid-layer (polycrystalline) are well defined with compositional uniformity and smooth interfaces.